

英飞凌汽车级80V 175°C N沟道

增强型OptiMOS™ 5 功率晶体管



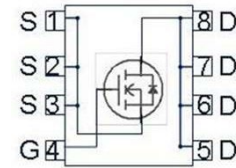
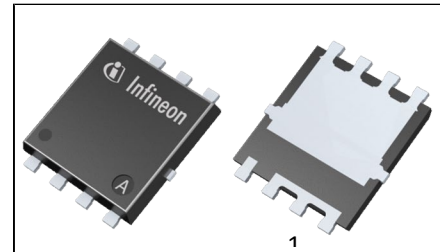
特点

- 适用于汽车应用的功率MOSFET
- N 沟道 - 增强型 - 逻辑电平
- MSL1 回流焊峰值温度高达 260°C
- 工作温度 175°C
- 绿色产品：符合 RoHS 标准
- 100% 雪崩测试

产品概述

V_{DS}	80	V
$R_{DS(on),max}$	7.5	mΩ
I_D	64	A

PG-TDSON-8-33



Type	Package	Marking
IAUC64N08S5L075	PG-TDSON-8-33	5N08L075

除非另有规定，否则均为 $T_j=25^\circ\text{C}$ 的**最大额定值**。

Parameter	Symbol	Conditions	Value	Unit
Drain current	I_D	$V_{GS}=10\text{ V}$, Chip limitation ^{1,2)}	64	A
		$V_{GS}=10\text{ V}$, DC current	64	
		$T_a=85^\circ\text{C}$, $V_{GS}=10\text{ V}$, R_{thJA} on 2s2p ^{2,3)}	13	
Pulsed drain current ²⁾	$I_{D,pulse}$	$T_c=25^\circ\text{C}$	256	
Avalanche energy, single pulse ²⁾	E_{AS}	$I_D=36\text{ A}$	56	mJ
Avalanche current, single pulse	I_{AS}	-	36	A
Gate source voltage	V_{GS}	-	±20	V
Power dissipation	P_{tot}	$T_c=25^\circ\text{C}$	75	W
Operating and storage temperature	T_j, T_{stg}	-	-55 ... +175	°C

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Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

热特性²⁾

Thermal resistance, junction - case	R_{thJC}	-	-	-	2.0	K/W
Thermal resistance, junction - ambient ⁴⁾	R_{thJA}	-	-	24.6	-	

除非另有规定，否则均为 $T_j=25^\circ\text{C}$ 的电气特性。

静态参数特性

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=1mA$	80	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=30\mu A$	1.2	1.6	2.0	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=80V, V_{GS}=0V, T_j=25^\circ\text{C}$	-	0.1	1	μA
		$V_{DS}=80V, V_{GS}=0V, T_j=85^\circ\text{C}^{2)}$	-	1	20	
Gate-source leakage current	I_{GSS}	$V_{GS}=20V, V_{DS}=0V$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=32A$	-	8.3	11.1	m Ω
		$V_{GS}=10V, I_D=32A$	-	6.3	7.5	
Gate resistance ²⁾	R_G	-	-	1.2	-	Ω

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

动态参数特性²⁾

Input capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=40V,$ $f=1MHz$	-	1620	2106	pF
Output capacitance	C_{oss}		-	260	338	
Reverse transfer capacitance	C_{rss}		-	17	26	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=40V, V_{GS}=10V,$ $I_D=32A, R_{G,ext}=3.5 \Omega$	-	3	-	ns
Turn-off delay time	$t_{d(off)}$		-	17	-	
Rise time	t_r		-	2	-	
Fall time	t_f		-	8	-	

栅极电荷特性²⁾

Gate to source charge	Q_{gs}	$V_{DD}=40V, I_D=32A,$ $V_{GS}=0 \text{ to } 10V$	-	5	7	nC
Gate to drain charge	Q_{gd}		-	6	9	
Gate charge total	Q_g		-	28	37	
Gate plateau voltage	$V_{plateau}$		-	3.1	-	V

反向二极管

Diode continuous forward current ²⁾	I_S	$T_C=25^\circ C$	-	-	64	A
Diode pulse current ²⁾	$I_{S,pulse}$	$T_C=25^\circ C$	-	-	256	
Diode forward voltage	V_{SD}	$V_{GS}=0V, I_F=32A,$ $T_J=25^\circ C$	-	0.9	1.2	V
Reverse recovery time ²⁾	t_{rr}	$V_R=40V, I_F=50A,$	-	36	-	ns
Reverse recovery charge ²⁾	Q_{rr}	$di_F/dt=100A/\mu s$	-	29	-	nC

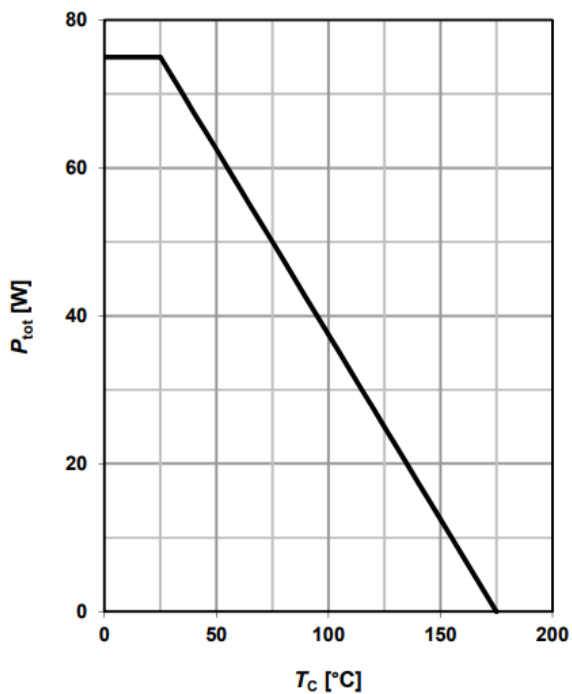
¹⁾ 实际上，电流能力受到包括客户特定的印刷电路板在内的整体系统设计的限制。

²⁾ 这些参数不经过生产测试，但经过设计和/或特性验证。

³⁾ 器件放置于根据JEDEC标准 (JESD51-5, -7) 定义的 2s2p FR4 印刷电路板上。印刷电路板垂直放置在静止空气中。

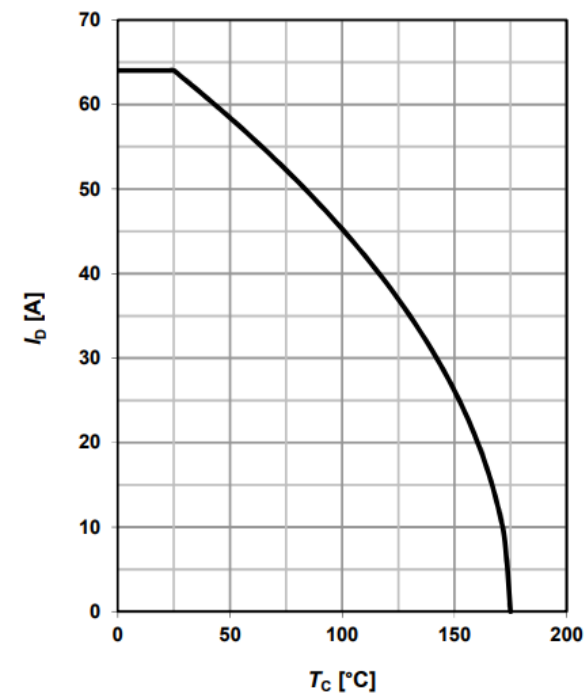
1 功率耗散

$$P_{\text{tot}} = f(T_c); V_{\text{GS}} = 10 \text{ V}$$



2 漏极电流

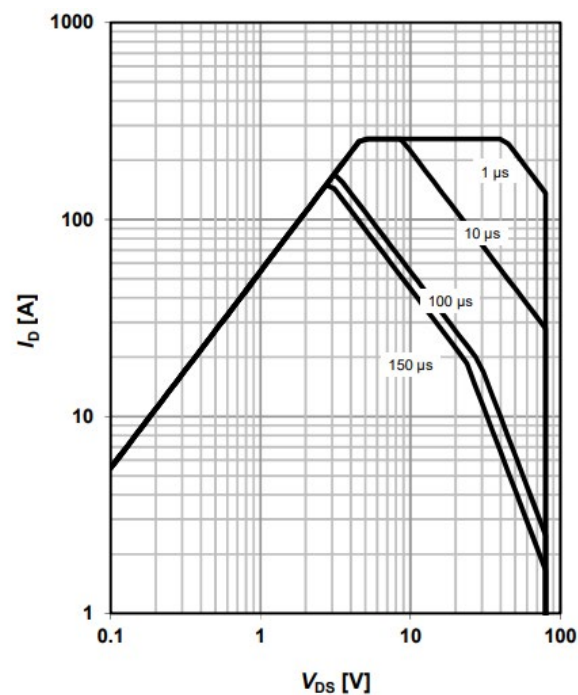
$$I_D = f(T_c); V_{\text{GS}} = 10 \text{ V}$$



3 安全工作区

$$I_D = f(V_{\text{DS}}); T_c = 25^\circ\text{C}; D = 0$$

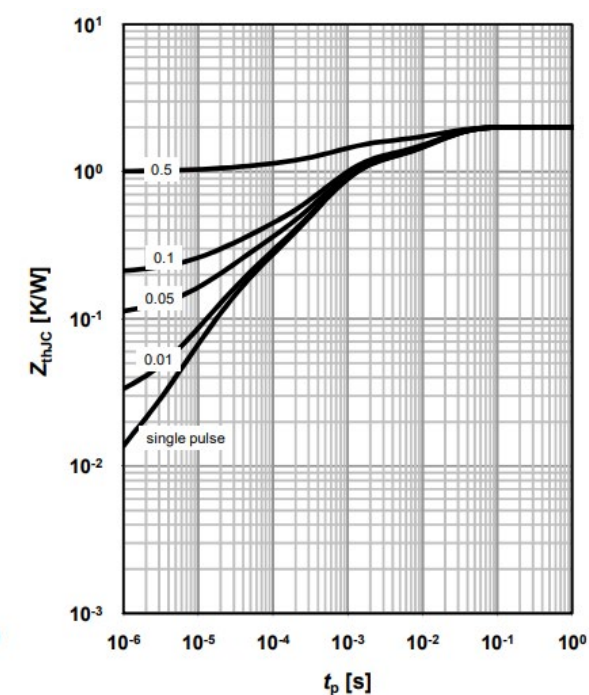
parameter: t_p



4 最大瞬态热阻抗

$$Z_{\text{thJC}} = f(t_p)$$

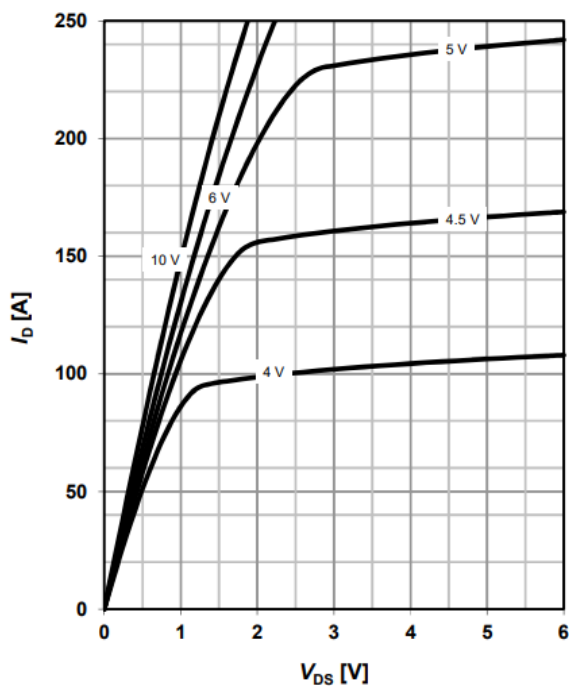
parameter: $D = t_p/T$



5 典型输出特性

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

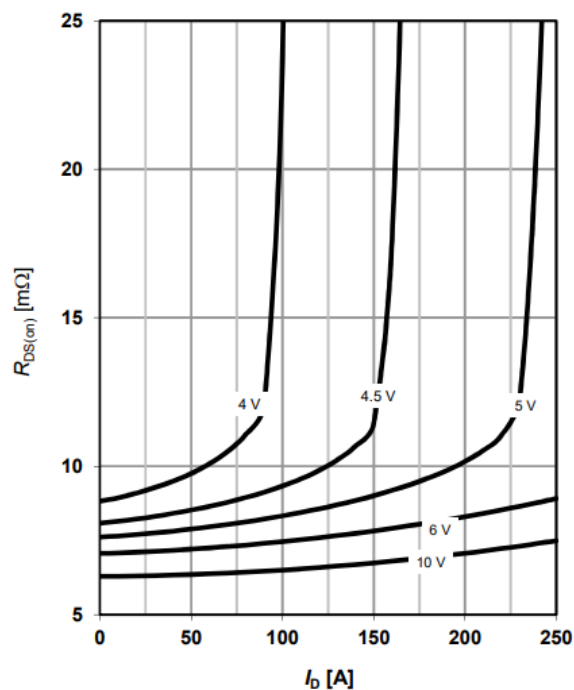
parameter: V_{GS}



6 典型漏源导通电阻

$$R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}$$

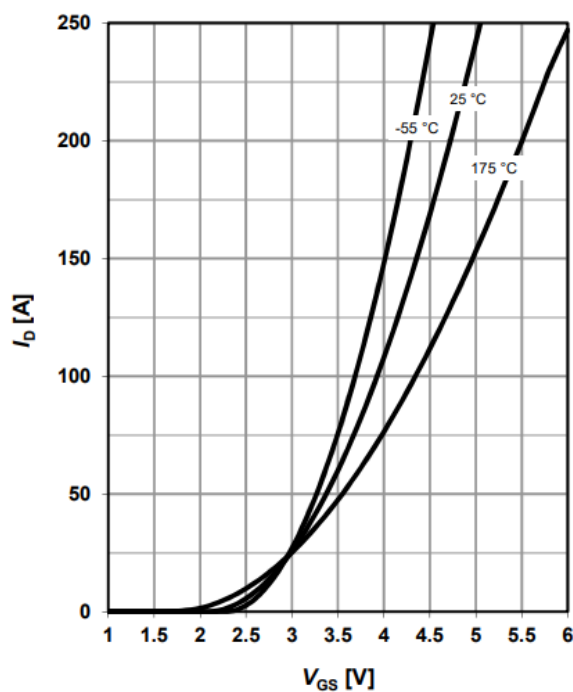
parameter: V_{GS}



7 典型转移特性

$$I_D = f(V_{GS}); V_{DS} = 6\text{V}$$

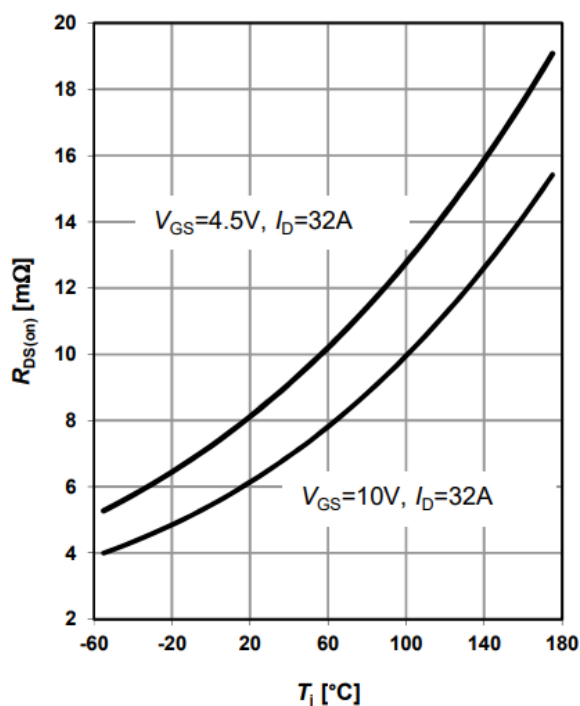
parameter: T_j



8 典型漏源导通电阻

$$R_{DS(on)} = f(T_j);$$

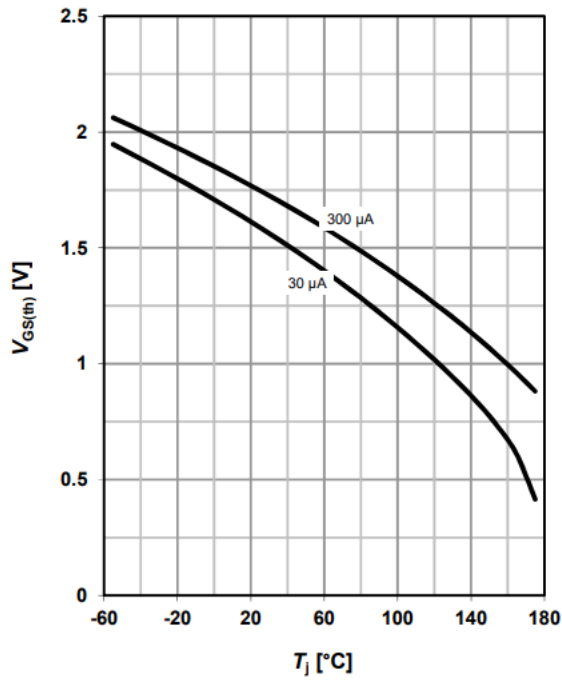
parameter: I_D, V_{GS}



9 典型栅极阈值电压

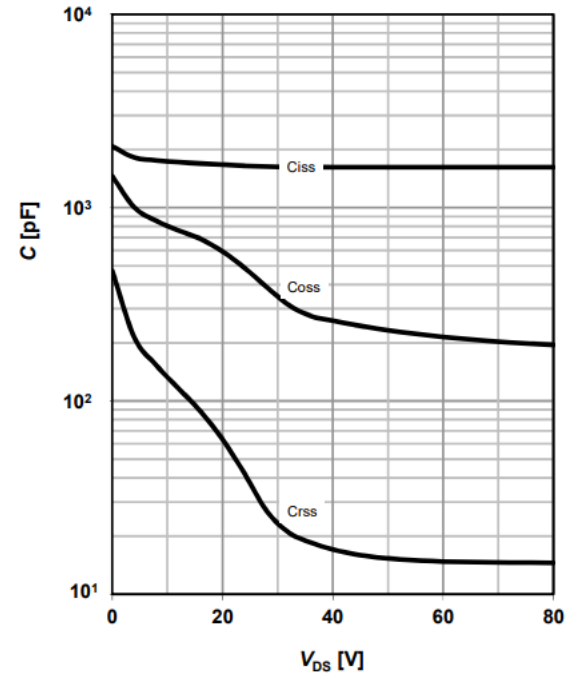
$$V_{GS(th)} = f(T_J); V_{GS} = V_{DS}$$

parameter: I_D



10 典型电容值

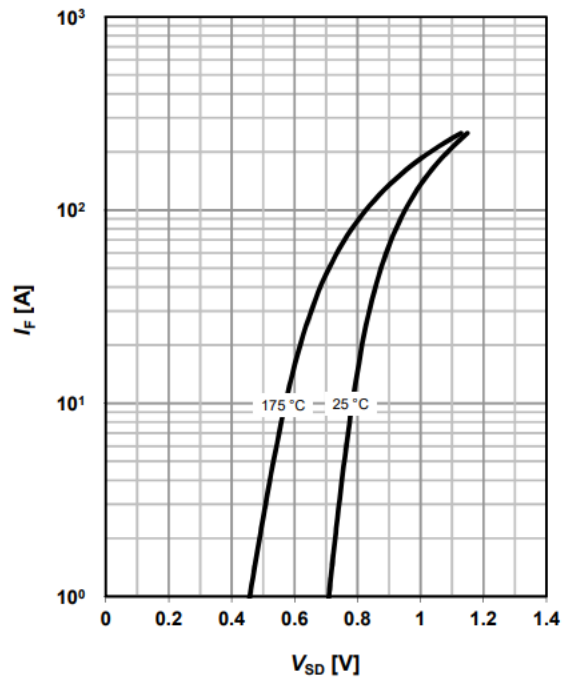
$$C = f(V_{DS}); V_{GS} = 0 V; f = 1 MHz$$



11 典型二极管正向导通特性

$$I_F = f(V_{SD})$$

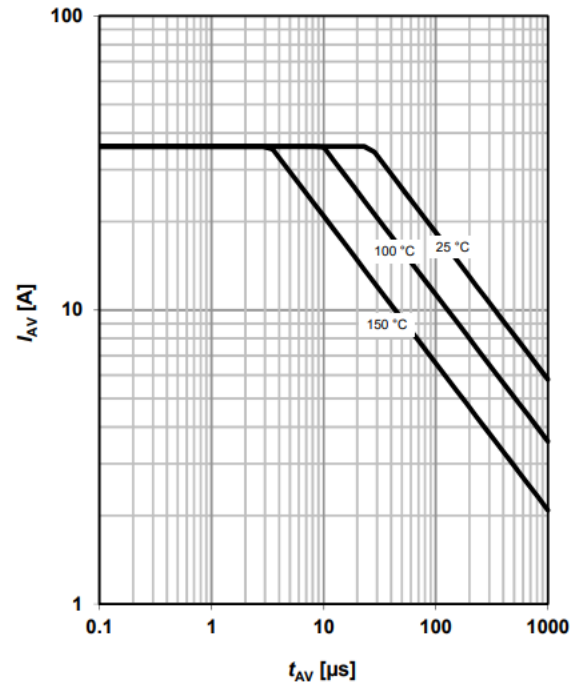
parameter: T_J



12 典型雪崩特性

$$I_{AS} = f(t_{AV})$$

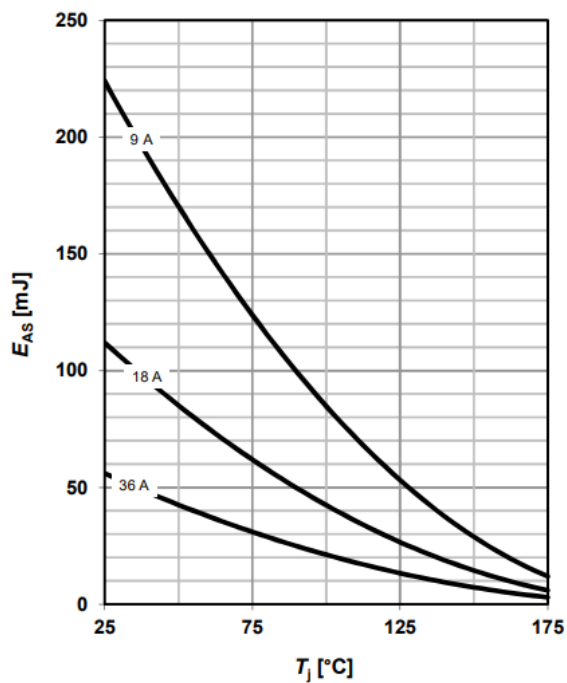
parameter: $T_{J(start)}$



13 典型雪崩能量

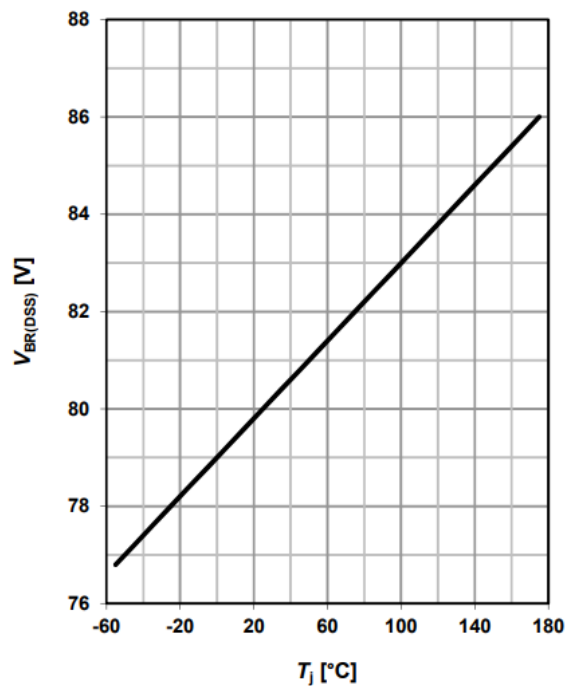
$$E_{AS} = f(T_j)$$

parameter: I_D



14 漏源击穿电压

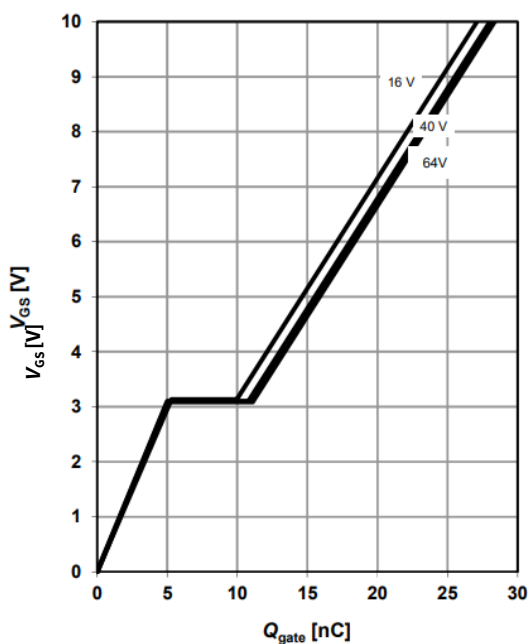
$$V_{BR(DSS)} = f(T_j); I_D = 1\text{ mA}$$



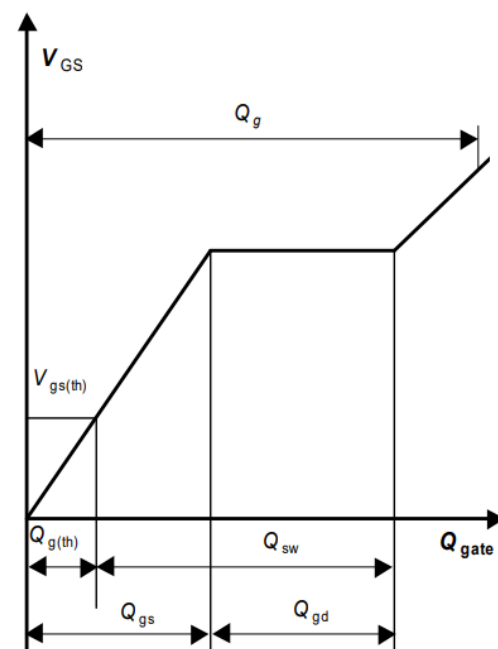
15 典型栅极电荷

$$V_{GS} = f(Q_{gate}); I_D = 32\text{ A pulsed}$$

parameter: V_{DD}



16 栅极充电波形



Technical drawing of a rectangular metal part with the following dimensions and features:

- Top View:**
 - Overall width: 5.15 ± 0.1
 - Overall height: 6.44 ± 0.1
 - Internal width: 4.44 ± 0.1
 - Internal height: 4.30 ± 0.1
 - Top edge features: 8 (left), 5 (right)
 - Bottom edge features: 1 (left), 4 (right)
 - Feature 1: INDEX MARKING
 - Feature 2: 0.13 ± 0.1
 - Feature 3: 0.9 ± 0.1
 - Feature 4: 0.4 ± 0.1
 - Feature 5: 0.48 ± 0.1
 - Feature 6: 0.25 ± 0.1
 - Feature 7: 0.12 ± 0.1
 - Feature 8: 0.4 ± 0.1
- Side View:**
 - Overall height: 5.48 ± 0.1
 - Internal height: 4.3 ± 0.1
 - Feature 1: 1 ± 0.1
 - Feature 2: 0.03
 - Feature 3: 0.25 ± 0.1
 - Feature 4: 0.12 ± 0.1
 - Feature 5: 0.4 ± 0.1
 - Feature 6: 0.48 ± 0.1
 - Feature 7: 0.13 ± 0.1
 - Feature 8: 0.12 ± 0.1
- Bottom View:**
 - Overall width: 5.15 ± 0.1
 - Overall height: 6.44 ± 0.1
 - Internal width: 4.44 ± 0.1
 - Internal height: 4.30 ± 0.1
 - Top edge features: 8 (left), 5 (right)
 - Bottom edge features: 1 (left), 4 (right)
 - Feature 1: INDEX MARKING
 - Feature 2: 0.13 ± 0.1
 - Feature 3: 0.9 ± 0.1
 - Feature 4: 0.4 ± 0.1
 - Feature 5: 0.48 ± 0.1
 - Feature 6: 0.25 ± 0.1
 - Feature 7: 0.12 ± 0.1
 - Feature 8: 0.4 ± 0.1

- 1) EXCLUDE MOLD FLASH
2) REMOVAL ON MOLD GATE, INTRUSION 0.1MM AND PROTRUSION 0.1MM
3) LEAD LENGTH UP TO ANTI FLASH LINE
4) ALL METAL SURFACE ARE PLATED, EXCEPT AREA OF CUT
ALL DIMENSIONS ARE IN UNITS MM
THE DRAWING IS IN COMPLIANCE WITH ISO 128 & PROJECTION METHOD 1 []

Figure 1 shows two detailed technical drawings of a PCB layout, illustrating dimensions in millimeters. The left drawing shows the copper layer, and the right drawing shows the solder mask and stencil apertures. The legend indicates that solid grey represents copper, hatched areas represent solder mask, and cross-hatched areas represent stencil apertures. All dimensions are in units mm.

Technical drawing of the 1000 Series PCB showing dimensions and pin 1 marking. The drawing includes a top view and a side view. The top view shows a rectangular board with dimensions 12 (width) and 6.9 (length). There are four circular mounting holes along the top edge, with a center-to-center distance of 8. The distance between the first and second mounting holes is 4. The board has a 0.3 thickness. The side view shows the board's profile with a 1.3 thickness. The drawing also shows the pin 1 marking on the board, which is a small circle with a dot in the center. The text 'PIN 1 INDEX MARKING' points to this marking. The drawing also shows the board's mounting holes and the dimensions of the board's mounting holes.

ALL DIMENSIONS ARE IN UNITS MM
THE DRAWING IS IN COMPLIANCE WITH ISO 128 & PROJECTION METHOD 1

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修订记录

Version	Date	Changes
Revision 1.0	2021-05-14	Final Data Sheet
Revision 1.1	2021-06-18	- Company logo size adjusted - Datasheet fine name updated



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